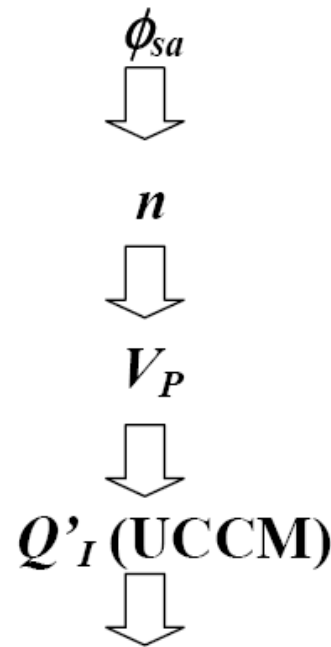


RECENT (and perhaps the final) ADVANCES IN THE ACM MODEL

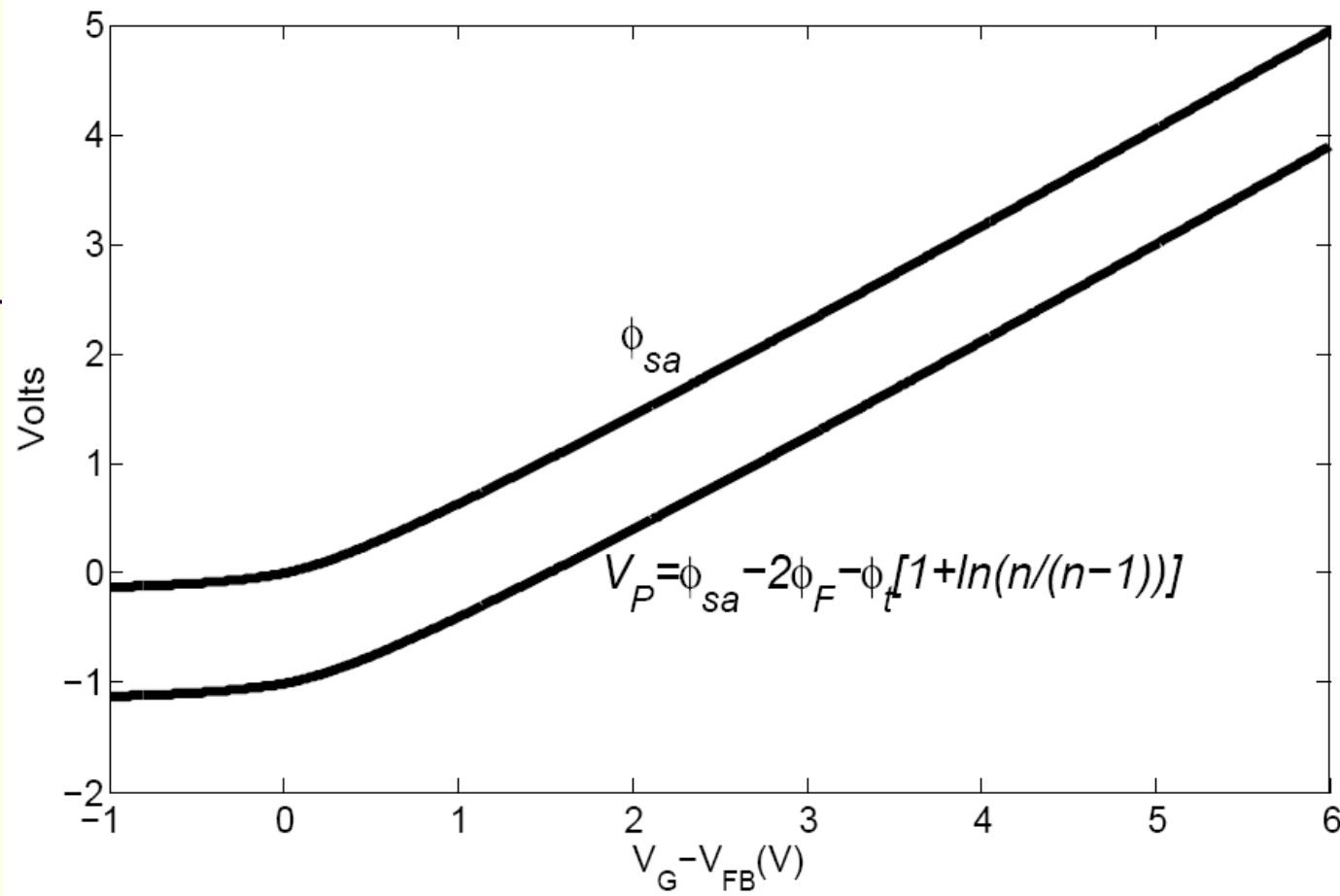
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- Decouple the input (electrostatic) and the output (transport) FET equations:
calculate the bulk capacitance C'_b for the surface potential ϕ_{sa} obtained disregarding the inversion charge density



I_D , total charges, ac parameters, $\phi_s = \phi_{sa} + Q'_I / n C'_{ox}$



- The ACM model is based on fully consistent approximations of the input and output equations of the MOSFET. The self-consistency of the ACM model allows the meaningful simulation of the series associations of transistors